

## PATENT

Atty Docket No.: 1000\$208-1

App. Ser. No.: 09/891,325

**IN THE CLAIMS:**

*Please find below a listing of all of the pending claims. The statuses of the claims are set forth in parentheses.*

## 1. (Currently Amended) An on-chip capacitor comprising:

a first electrode formed during a first deposition of a first metal layer of a multi-level semiconductor device;

a substantially-thin first dielectric layer configured to be deposited over deposited on an interface of said first electrode, the first dielectric layer having a first dielectric constant;  
and

a second electrode formed during a second deposition of a second metal layer of said multi-level deposition device, wherein said second electrode is ~~formed over~~ deposited on an interface of said substantially-thin first dielectric layer, wherein said on-chip capacitor is formed in a crossover area of said first metal layer and said second metal layer of said multi-level semiconductor device; and

a second dielectric layer also deposited on the interface of said first dielectric layer, the second dielectric layer having a second dielectric constant smaller than the first dielectric constant of the first dielectric layer.

2. (Original) The on-chip capacitor according to claim 1, wherein an angle of intersection between said first metal layer and said second metal layer is between zero and ninety degrees.

3. (Original) The on-chip capacitor according to claim 1, wherein said first electrode and said second electrode are configured to be substantially parallel.

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4. (Original) The on-chip capacitor according to claim 3, wherein said first electrode and said second electrode are further configured to be overlapping.

5. (Original) The on-chip capacitor according to claim 1, wherein said first electrode and said second electrode are configured as a rectangular planar structure.

6. (Original) The on-chip capacitor according to claim 5, wherein said first electrode and said second electrode are substantially parallel and overlapping.

7. (Currently Amended) The on-chip capacitor according to claim 1, wherein said substantially thin first dielectric material layer comprises a composite of materials.

8. (Currently Amended) ~~The on-chip capacitor according to claim 7;~~ An on-chip capacitor comprising;

a first electrode formed during a first deposition of a first metal layer of a multi-level semiconductor device;

a substantially thin dielectric layer configured to be deposited over said first electrode;  
and

a second electrode formed during a second deposition of a second metal layer of said multi-level deposition device, wherein said second electrode is formed over said substantially thin dielectric layer, wherein said on-chip capacitor is formed in a crossover area of said first metal layer and said second metal layer of said multi-level semiconductor device; wherein

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said substantially thin dielectric layer comprises a composite of materials that includes PZT  
and platinum.

9. (Currently Amended) The on-chip bypass capacitor according to claim 1, wherein a  
dielectric constant of said ~~substantially thin~~ first dielectric material layer is substantially high.

10. (Currently Amended) The on-chip bypass capacitor according to claim 9, wherein said  
~~substantially thin~~ first dielectric material layer includes silicon nitride.

11. (Currently Amended) The on-chip bypass capacitor according to claim 10, wherein said  
thickness of said ~~substantially thin~~ first dielectric material layer is between 50 to 100  
angstroms.

12. (New) The on-chip capacitor according to claim 1, wherein the second electrode is also  
deposited on an interface of the second dielectric layer, and the second dielectric layer is  
predetermined to be thicker than the first dielectric layer.